IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

SONG, W. et al. Atty. Ref.: 2826-11

Serial No. unknown Group:

Filed: February 21, 2002 Examiner:

For: A METHOD OF PATTERNING A SUBSTRATE

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February 21, 2002

Assistant Commissioner for Patents
Washington, DC 20231

Sir:

PRELIMINARY AMENDMENT

In order to place the above-identified application in better condition for examination, please amend the application as follows:

IN THE CLAIMS

Please substitute the following amended claims for corresponding claims previously presented. A copy of the amended claims showing current revisions is attached.

4. The method of claim 2, wherein the thickness of the liquid film is in the range of several micrometers to several tens of micrometers.

5. The method of claim 1, wherein the liquid vapour is jetted with a gas to carry the liquid vapour onto the substrate surface.

7. The method of claim 1, wherein the laser directs laser energy in pulses of predetermined duration.

9. The method of claim 1, wherein the laser fluence of the laser is more than the etching threshold of the substrate.

11. The method of claim 1, wherein the substrate surface has an ITO film onto which the liquid film is formed.

12. The method of claim 1, wherein the substrate has one or more layers.

15. The method of claim 1, wherein the substrate is substantially composed of glass, quartz and/or silicon.

16. The method of claim 1, wherein the substrate is an ITO film IC package, silicon wafer, conductor, semiconductor or insulator.

REMARKS

Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached page(s) is captioned "**Version With Markings To Show Changes Made**."

Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS

4. The method of claim 2 ~~or 3~~, wherein the thickness of the liquid film is in the range of several micrometers to several tens of micrometers.

5. The method of ~~any one of~~ claim~~s~~ 1 ~~to 4~~, wherein the liquid vapour is jetted with a gas to carry the liquid vapour onto the substrate surface.

7. The method of ~~any one of the preceding~~ claim~~s~~ 1, wherein the laser directs laser energy in pulses of predetermined duration.

9. The method of ~~any of the preceding~~ claim~~s~~ 1, wherein the laser fluence of the laser is more than the etching threshold of the substrate.

11. The method of ~~any one of the preceding~~ claim~~s~~ 1, wherein the substrate surface has an ITO film onto which the liquid film is formed.

12. The method of ~~any one of the preceding~~ claim~~s~~ 1, wherein the substrate has one or more layers.

15. The method of ~~any one of the preceding~~ claim~~s~~ 1, wherein the substrate is substantially composed of glass, quartz and/or silicon.

16. The method of ~~any one of the preceding~~ claim~~s~~ 1, wherein the substrate is an ITO film IC package, silicon wafer, conductor, semiconductor or insulator.